Subminiature Point Contact Diodes* (See Outline Drawing 37)

Types	MAXIMUM Peak Inverse Voltage Volts	MAXIMUM Average Forward Current[1] ma	MAXIMUM Surge Current[2] ma	MAXIMUM Reverse Current I_R 25°C μa	MAXIMUM Reverse Current I_R 150°C μa	TOTAL CAPACITANCE V_R= −2 volts pf	TOTAL CAPACITANCE V_R= −40 volts pf
12P2 through 19P2	200-10	40	120	0.5	100	0.4	0.3
23J2 through 28J2	200-10	60	120	0.2[3]	100	0.4	0.3

NOTES: *Made in France for General Electric by the Societe Europeenne Des Semiconducteurs (SESCO).
(1) For types 12P2 and 19P2 this parameter is 60 ma
(2) For types 12P2 and 19P2 this parameter is 180 ma
(3) For 90% of the production, the inverse current is less than 0.1 μa.

Matched Pairs and Quads (See Outline Drawing No. 43)

Type	Forward Voltage V_F Volts	MAXIMUM Reverse Current I_R 25°C μa	MAXIMUM Reverse Current I_R 150°C μa	Min. Breakdown Voltage V I_R=5 μa Volts	ΔV_F—Max. Forward Voltage difference between diodes in pairs or quads (T_A=−55°C to +125°C) I_F=0.1 to 10 ma mv	ΔV_F I_F=10 to 50 ma mv	MAX. Forward Current Steady State DC ma	Comments
MP-1 (1N4306)	See above*	.05 @ 50V	50 @ 50V	75	10	20		(MP-1 was formerly 1N4306) Matched pairs in molded package. (Silicon Signal Diodes)
MP-2	1.0 @ 10 ma	.10 @ 30V	100 @ 30V	40	10	50		
MQ-1 (1N4307)	See above*	.05 @ 50V	50 @ 50V	75	10	20		(MQ-1 was formerly 1N4307) Matched quads in molded package. (Silicon Signal Diodes)
MQ-2	1.0 @ 10 ma	.10 @ 30V	100 @ 30V	40	10	50		

*

Type	I_F ma	Forward Voltage V_F Min.	Forward Voltage V_F Max.
MP-1 and MQ-1	.100	.440	.550
	1	.560	.670
	10	.670	.810
	100	.750	1.000

Snap-off Diodes (See Outline Drawing No. 37)

Type	Power Dissipation 25°C mw	Peak Surge Current 1 μs amperes	MINIMUM Breakdown Voltage I_R=5μamps B_V Volts	MAXIMUM Capacitance V_R=0V, f=1 mc C_o pf	MINIMUM Stored Charge Q_t pc/ma	TYP. Snap-off time Ts=2 nsec. I_F=20 ma t_{sp} nsec.	MAX. Snap-off time Ts=2 nsec. I_F=20 ma t_{sp} nsec.	TYP. Snap-off time Ts=2 nsec. I_F=100 ma tsp nsec.	MAX. Snap-off time Ts=2 nsec. I_F=100 ma tsp nsec.
SSA-550[2]/554[3]	250	2	12	1.5	20	0.3	0.5		
SSA-551[2]/555[3]	250	2	8	4.0	20	0.3	0.5		
SSA-552[2]/556[3]	250	2	12	1.5	1.0			0.2[1]	0.4
SSA-553[2]/557[3]	250	2	8	4.0	1.0			0.2[1]	0.4

NOTES: (1) Limited by resolution time of test equipment. (2) DO-7 package. (3) Micro Silicon Diode—see Specifications 75, 28 for outline dimensions.

Microphoto Diodes*[1] — NPN (See Outline Drawing No. 45)

Type	MAX.[2] Bias Volts	MAX.[2] P_C mw	MAX. DARK CURRENT at 24 vdc μa	TYPICAL DARK CURRENT at 24 vdc μa	TYPICAL SENSITIVITY[3,4] at 250 ft. —c. μa/ft. —c.	TYPICAL SENSITIVITY[3,4] at 1000 ft. —c. μa/ft. —c.	TYPICAL PHOTOCURRENT DECAY TIMER μsec.
31F2	40	50	0.1	0.02	0.2	0.8	1
32F2	40	50	0.1	0.02	0.5	1.5	1
33F2	40	50	0.1	0.02	0.9	2.2	1
34F2	40	50	0.1	0.02	1.6	5.0	1

NOTES: *Made in France for General Electric by the Societe Europeenne Des Semiconducteurs (SESCO).
(1) All specs at 25°C unless noted otherwise.
(2) Storage temperature on all types is −65 to +125°C. Operating temperature on all types is −65 to +100°C.
(3) Light source—Tungsten Filament Lamp Operated at a Color Temperature of 2870°K.
(4) Maximum Sensitivity wave length 0.9 to 1.0 microns.